## **SKT 551**



## **Capsule Thyristors**

### **Thyristors**

#### **SKT 551**

#### **Features**

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- Shallow design with single sided cooling
- · International standard case
- Off-state and reverse voltages up to 1800 V
- · Amplifying gate

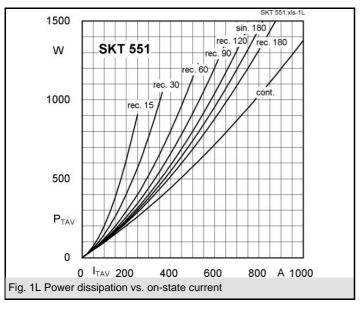
#### **Typical Applications**

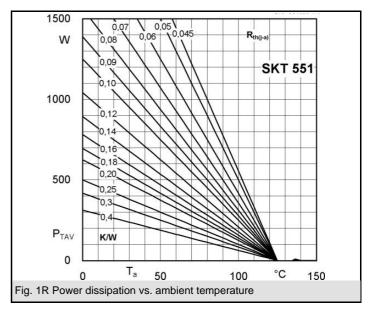
- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers
  - (e. g. for temperature control)
- Recommended snubber network e.g. for  $V_{VRMS} \le 400 \text{ V}$ : R = 33  $\Omega/32$  W, C = 0,47  $\mu F$

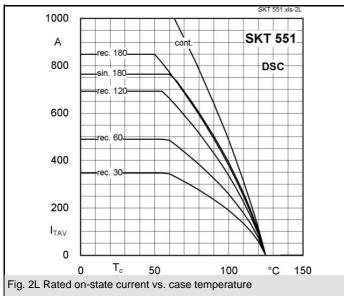
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>TRMS</sub> = 1200 A (maximum value for continuous operation)		
V	V	I <sub>TAV</sub> = 550 A (sin. 180; DSC; T <sub>c</sub> = 85 °C)		
900	800	SKT 551/08E		
1300	1200	SKT 551/12E		
1500	1400	SKT 551/14E		
1700	1600	SKT 551/16E		
1900	1800	SKT 551/18E		

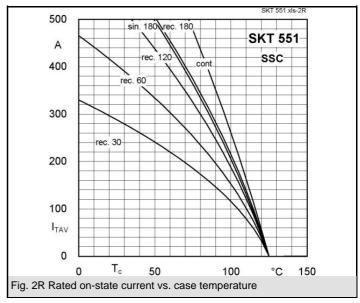
Symbol	Conditions	Values	Units
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 100 (85) °C;	391 (550 )	Α
I <sub>D</sub>	2 x P8/180; T <sub>a</sub> = 45 °C; B2 / B6	390 / 560	Α
_	2 x P8/180 F; T <sub>a</sub> = 35 °C; B2 / B6	980 /1340	Α
I <sub>RMS</sub>	2 x P8/180; T <sub>a</sub> = 45 °C; W1C	430	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	9000	Α
	$T_{vj} = 125 ^{\circ}\text{C}; 10 \text{ms}$	8000	Α
i²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	405000	A²s
	T <sub>vj</sub> = 125 °C; 8,3 10 ms	320000	A²s
V <sub>T</sub>	T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 1500 A	max. 1,65	V
$V_{T(TO)}$	T <sub>vi</sub> = 125 °C	max. 0,925	V
r <sub>T</sub>	T <sub>vi</sub> = 125 °C	max. 0,45	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 125  ^{\circ}\text{C},  V_{RD} = V_{RRM},  V_{DD} = V_{DRM}$	max. 60	mA
t <sub>gd</sub>	$T_{vj} = 25 \text{ °C; } I_{G} = 1 \text{ A; } di_{G}/dt = 1 \text{ A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_{\rm D} = 0.67 * V_{\rm DRM}$	1	μs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 125	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 1000	V/µs
$t_q$	$T_{vi} = 125 ^{\circ}\text{C}$ ,	50 150	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	150 / 500	mA
$I_L$	$T_{vj} = 25  ^{\circ}\text{C};  R_{G} = 33  \Omega;  \text{typ. / max.}$	500 / 2000	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.	min. 3	V
$I_{GT}$	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 250	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	$T_{vj} = 125 ^{\circ}\text{C};  \text{d.c.}$	max. 10	mA
R <sub>th(j-c)</sub>	cont.; DSC	0,045	K/W
R <sub>th(j-c)</sub>	sin. 180; DSC / SSC	0,047 / 0,1	K/W
R <sub>th(j-c)</sub>	rec. 120; DSC / SSC	0,054 / 0,113	K/W
R <sub>th(c-s)</sub>	DSC / SSC	0,012 / 0,024	K/W
$T_{vj}$		- 40 <b>+</b> 125	°C
$T_{stg}$		- 40 <b>+</b> 130	°C
V <sub>isol</sub>		-	V~
F	mounting force	5,2 8	kN
а			m/s²
m	approx.	105	g
Case		B 11	

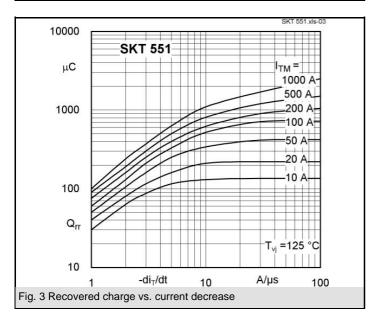


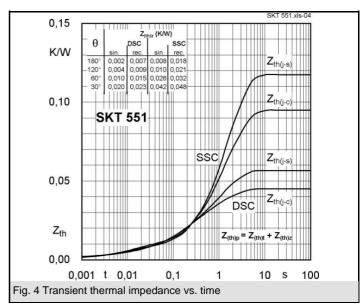




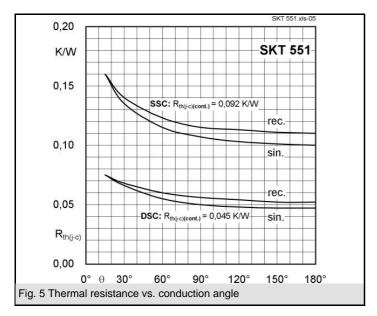


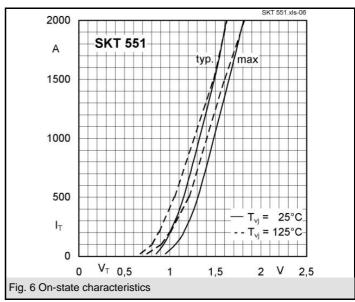


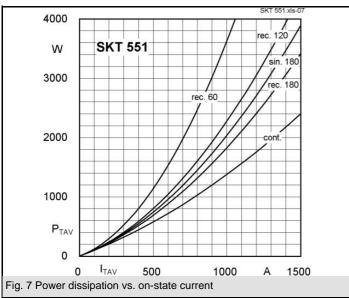


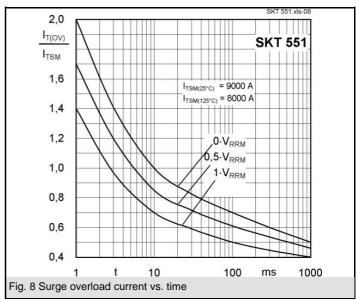


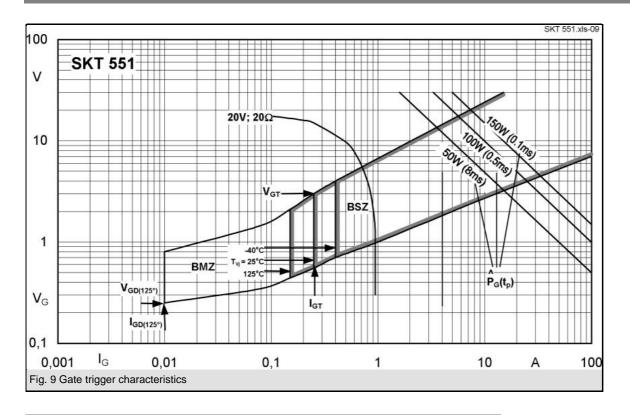
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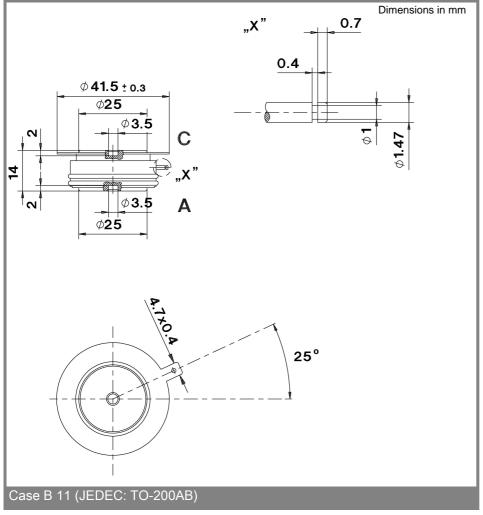


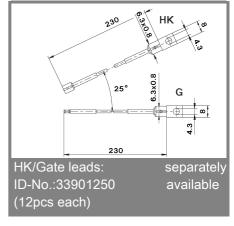












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